

IPS0151/IPS0151S

FULLY PROTECTED POWER MOSFET SWITCH

Features

- Over temperature shutdown
- Over current shutdown
- Active clamp
- Low current & logic level input
- E.S.D protection

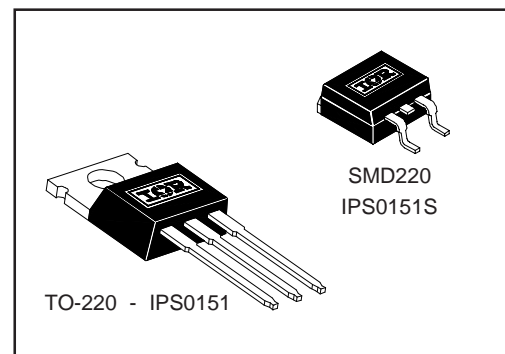
Description

The IPS0151/IPS0151S are fully protected three terminal SMART POWER MOSFETs that feature over-current, over-temperature, ESD protection and drain to source active clamp. These device combine a HEXFET POWER MOSFET and a gate driver. They offer full protection and high reliability required in harsh environments. The driver allows short switching times and provides efficient protection by turning OFF the power MOSFET when the temperature exceeds 165°C or when the drain current reaches 35A. These device restart once the input is cycled. The avalanche capability is significantly enhanced by the active clamp and covers most inductive load demagnetizations.

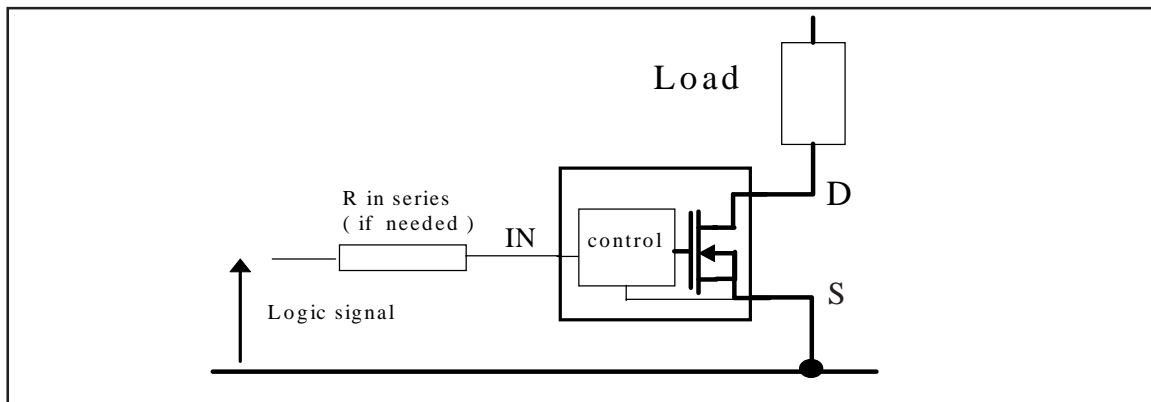
Product Summary

$R_{ds(on)}$	25m Ω (max)
V_{clamp}	50V
$I_{shutdown}$	35A
T_{on}/T_{off}	1.5 μ s

Available Package



Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicates sustained limits beyond which damage to the device may occur. All voltage parameters are referenced to SOURCE lead. (T_{Ambient} = 25°C unless otherwise specified). PCB mounting uses the standard footprint with 70 μm copper thickness.

Symbol	Parameter	Min.	Max.	Units	Test Conditions
V _{ds}	Maximum drain to source voltage	—	47	V	
V _{in}	Maximum Input voltage	-0.3	7		
I _{in, max}	Maximum IN current	-10	+10	mA	
I _{sd cont.}	Diode max. continuous current ⁽¹⁾ (r _{th} =62°C/W) IPS0151 (r _{th} =5°C/W) IPS0151 (r _{th} =80°C/W) IPS0151S	—	2.8	A	TO220 free air
		—	35		TO220 + good cooling
		—	2.2		SMD220 Std footprint
I _{sd pulsed}	Diode max. pulsed current ⁽¹⁾	—	45		
P _d	Maximum power dissipation ⁽¹⁾ (r _{th} =62°C/W) IPS0151 (r _{th} =80°C/W) IPS0151S	—	2	W	
		—	1.56		
ESD1	Electrostatic discharge voltage (Human Body)	—	5	kV	C=100pF, R=1500Ω,
ESD2	Electrostatic discharge voltage (Machine Model)	—	0.6		C=200pF, R=0Ω,
T _{j max.}	Max. storage & operating junction temp.	-40	+150	°C	
T _{lead}	Lead temperature (soldering, 10 seconds)	—	300		

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
R _{th 1}	Thermal resistance free air	—	55	62	°C/W	TO-220
R _{th 2}	Thermal resistance junction to case	—	2	—		
R _{th 1}	Thermal resistance with standard footprint	—	58	80		D ² PAK (SMD220)
R _{th 2}	Thermal resistance with 1" square footprint	—	35	60		
R _{th 3}	Thermal resistance junction to case	—	2	—		

Recommended Operating Conditions

These values are given for a quick design. For operation outside these conditions, please consult the application notes.

Symbol	Parameter	Min.	Max.	Units
V _{ds (max)}	Continuous drain to source voltage	—	35	V
V _{IH}	High level input voltage	4	6	
V _{IL}	Low level input voltage	0	0.5	
I _{ds} T _{amb} =85°C	Continuous drain current (T _{Ambient} = 85°C, I _N = 5V, r _{th} = 60°C/W, T _j = 125°C) IPS0151 (T _{Ambient} = 85°C, I _N = 5V, r _{th} = 80°C/W, T _j = 125°C) IPS0151S	—	4.3	A
		—	3.8	
R _{in}	Recommended resistor in series with IN pin	0.2	5	kΩ
T _{r-in (max)}	Max recommended rise time for IN signal (see fig. 2)	—	1	μS
F _{r-lsc} ⁽²⁾	Max. frequency in short circuit condition (V _{cc} = 14V)	0	1	kHz

(1) Limited by junction temperature (pulsed current limited also by internal wiring)

(2) Operations at higher switching frequencies is possible. See Appl. Notes.

Static Electrical Characteristics

(T_j = 25°C unless otherwise specified.)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
R _{ds(on)}	ON state resistance	T _j = 25°C	10	20	25	mΩ	V _{in} = 5V, I _{ds} = 1A
		T _j = 150°C	—	35	45		
I _{dss1} @T _j =25°C	Drain to source leakage current	0	0.5	25	μA	V _{CC} = 14V, T _j = 25°C	
I _{dss2} @T _j =25°C	Drain to source leakage current	0	5	50		V _{CC} = 40V, T _j = 25°C	
V _{clamp 1}	Drain to source clamp voltage 1	47	52	56	V	I _d = 20mA (see Fig.3 & 4)	
V _{clamp 2}	Drain to source clamp voltage 2	50	55	60		I _d =I _{shutdown} (see Fig.3 & 4)	
V _{in clamp}	IN to source clamp voltage	7	8.1	9.5		I _{in} = 1 mA	
V _{in th}	IN threshold voltage	1	1.6	2		I _d = 50mA, V _{ds} = 14V	
I _{in, -on}	ON state IN positive current	25	90	200	μA	V _{in} = 5V	
I _{in, -off}	OFF state IN positive current	50	130	250		V _{in} = 5V over-current triggered	

Switching Electrical Characteristics

V_{CC} = 14V, Resistive Load = 3Ω, Rin_{put} = 50Ω, 100μsec pulse, T_j = 25°C, (unless otherwise specified).

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
T _{on}	Turn-on delay time	0.05	0.25	0.6	μsec	See figure 2
T _r	Rise time	0.2	0.9	1.5		
T _{rf}	Time to (final R _{ds(on)} 1.3%)	—	3.8	—		
T _{off}	Turn-off delay time	0.8	1.5	2		See figure 2
T _f	Fall time	0.4	1.1	2		
Q _{in}	Total gate charge	—	30	—	nC	V _{in} = 5V

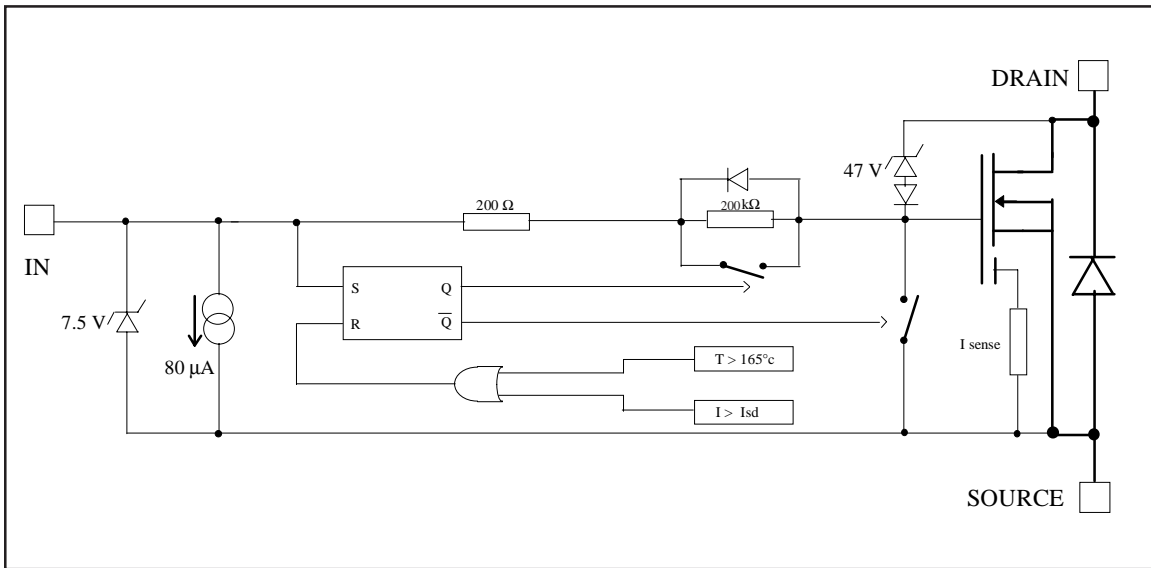
Protection Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
T _{sd}	Over temperature threshold	—	165	—	°C	See fig. 1
I _{sd}	Over current threshold	20	35	50	A	See fig. 1
V _{in,min,prot}	Minimum IN voltage for protection	1.5	2.3	3	V	
T _{reset}	Minimum time to reset protection	2	10	40	μs	V _{in} = 0V
EOI_OT	Short circuit energy (see application note)		400		μJ	V _{CC} = 14V

IPS0151/IPS0151S

Functional Block Diagram

All values are typical



Lead Assignments

<p>2 (D)</p> <p>1 2 3 In D S TO-220</p>	<p>2 (D)</p> <p>1 3 In D S</p>
IPS0151	IPS0151S
Part Number	

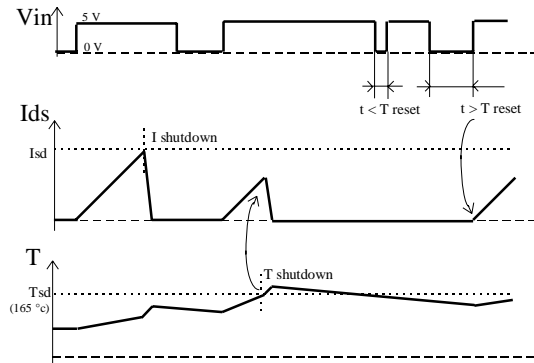


Figure 1 - Timing diagram

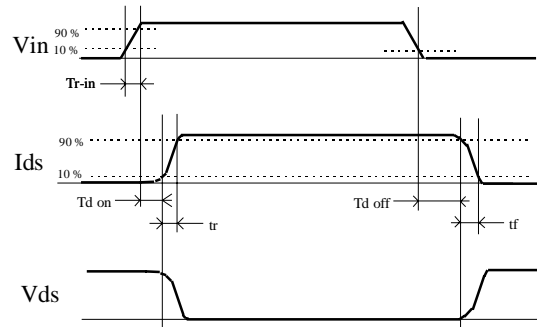


Figure 2 - IN rise time & switching time definitions

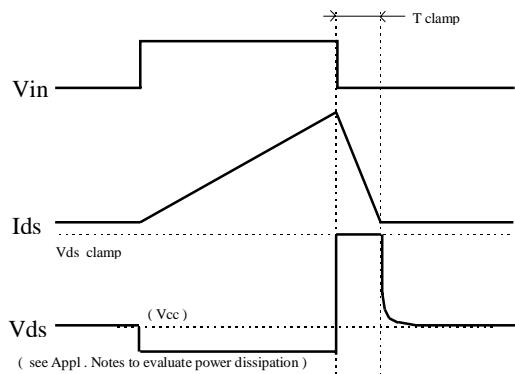


Figure 3 - Active clamp waveforms

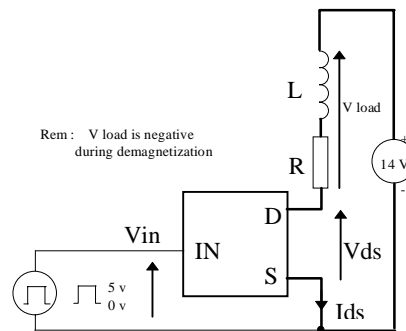


Figure 4 - Active clamp test circuit

All curves are typical values with standard footprints. Operating in the shaded area is not recommended.

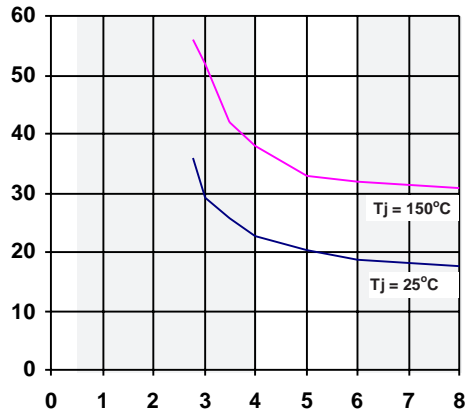


Figure 5 - Rds ON (mΩ) Vs Input Voltage (V)

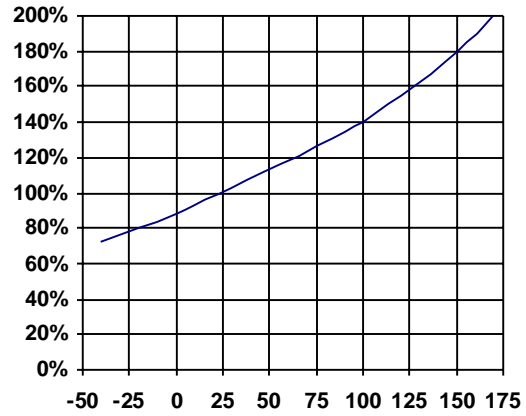


Figure 6 - Normalised Rds ON (%) Vs Tj (°C)

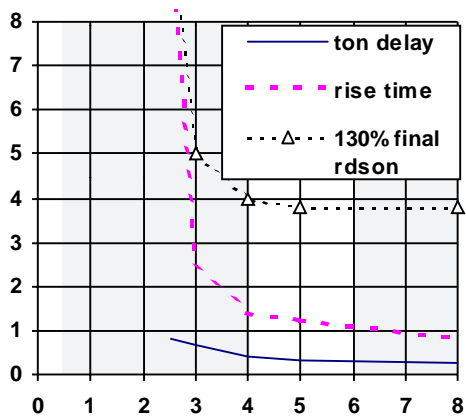


Figure 7 - Turn-ON Delay Time, Rise Time & Time to 130% final Rds(on) Vs Input Voltage (V)

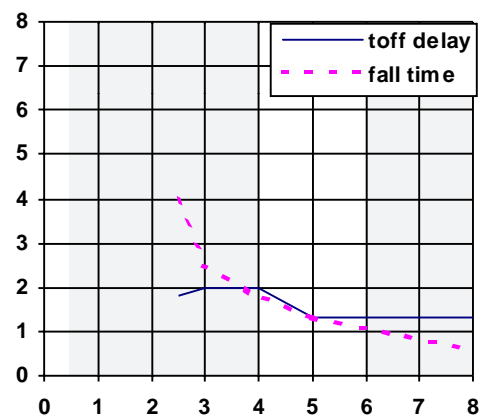


Figure 8 - Turn-OFF Delay Time & Fall Time (us) Vs Input Voltage (V)

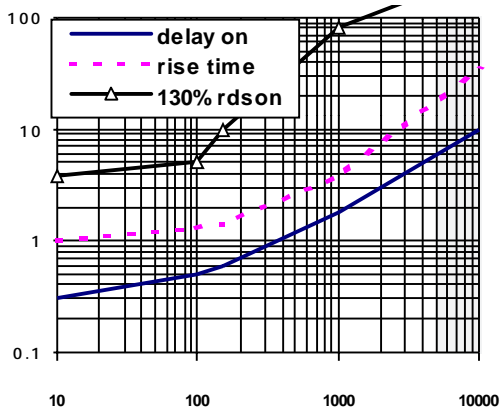


Figure 9 - Turn-ON Delay Time, Rise Time & Time to 130% final R_{ds(on)} Vs IN Resistor (Ω)

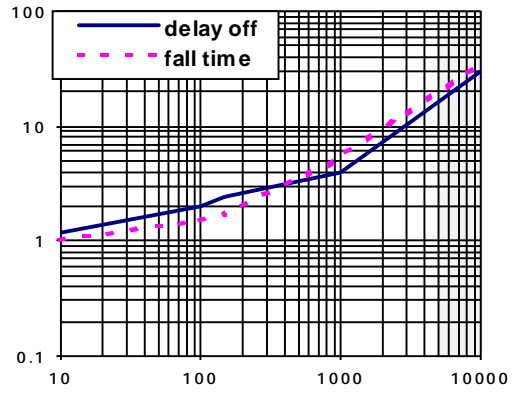


Figure 10 - Turn-OFF Delay Time & Fall Time (us) Vs IN Resistor (Ω)

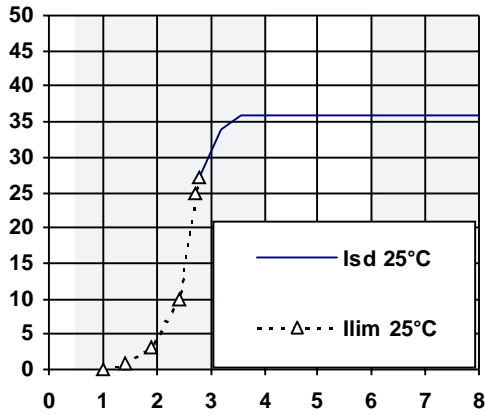


Figure 11 - Current lim. & I_{shutdown} (A) Vs V_{in} (V)

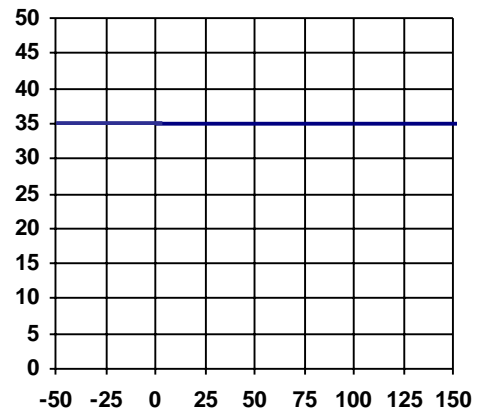


Figure 12 - Over-current (A) Vs Temperature (°C)

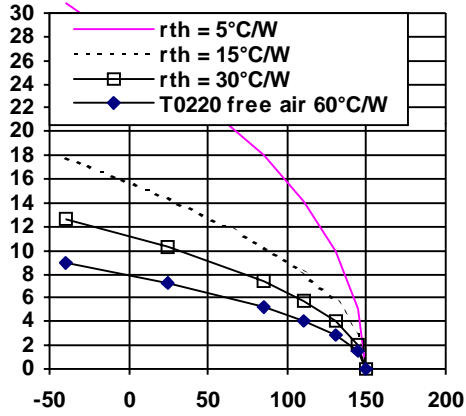


Figure 13a - Max.Cont. Ids (A) Vs Amb. Temperature (°C) - IPS0151

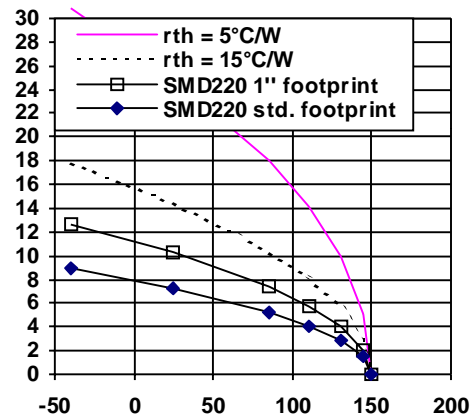


Figure 13b - Max.Cont. Ids (A) Vs Amb. Temperature (°C) - IPS0151S

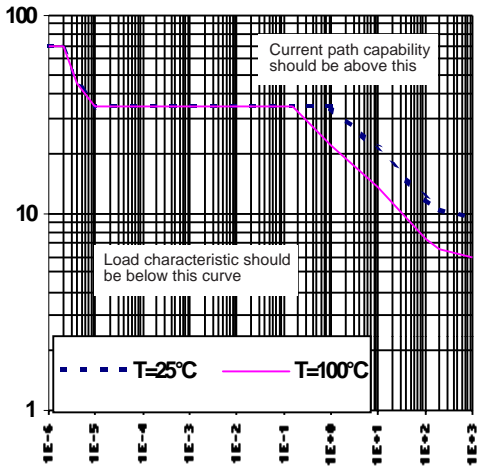


Figure 14 - Ids (A) Vs Protection Resp. Time (s) IPS0151 & IPS0151S

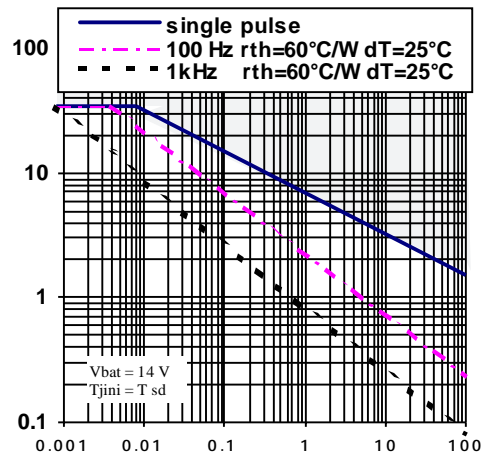


Figure 15 - Iclamp (A) Vs Inductive Load (mH)

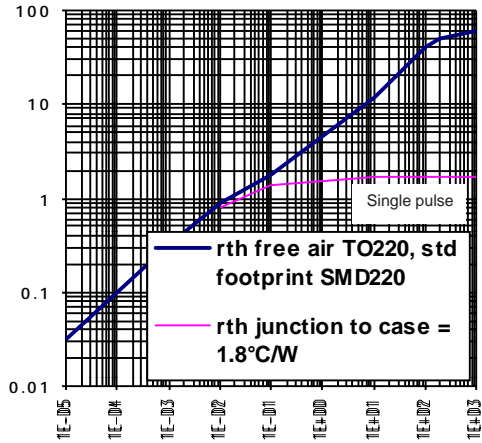


Figure 16 - Transient Thermal Imped. (°C/W) Vs Time (s) - IPS0151/IPS051S

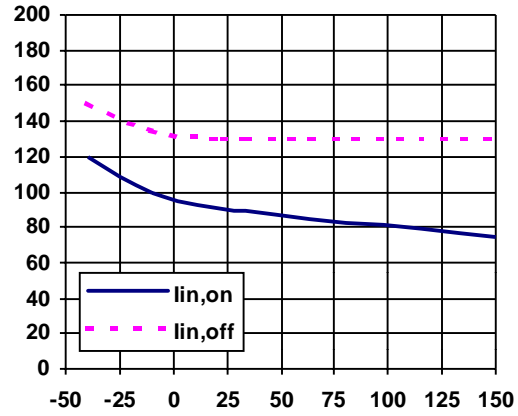


Figure 17 - Input current (µA) Vs Junction (°C)

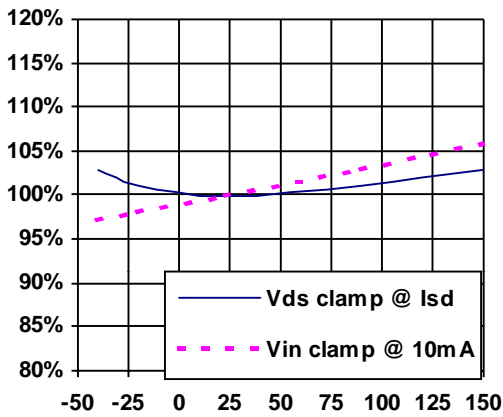


Figure 18 - Vin clamp and V clamp2 Vs Tjunction (°C)

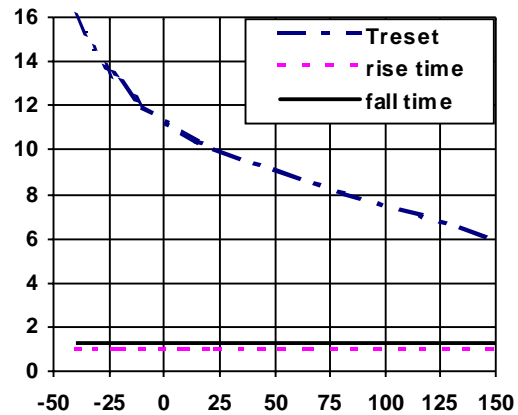
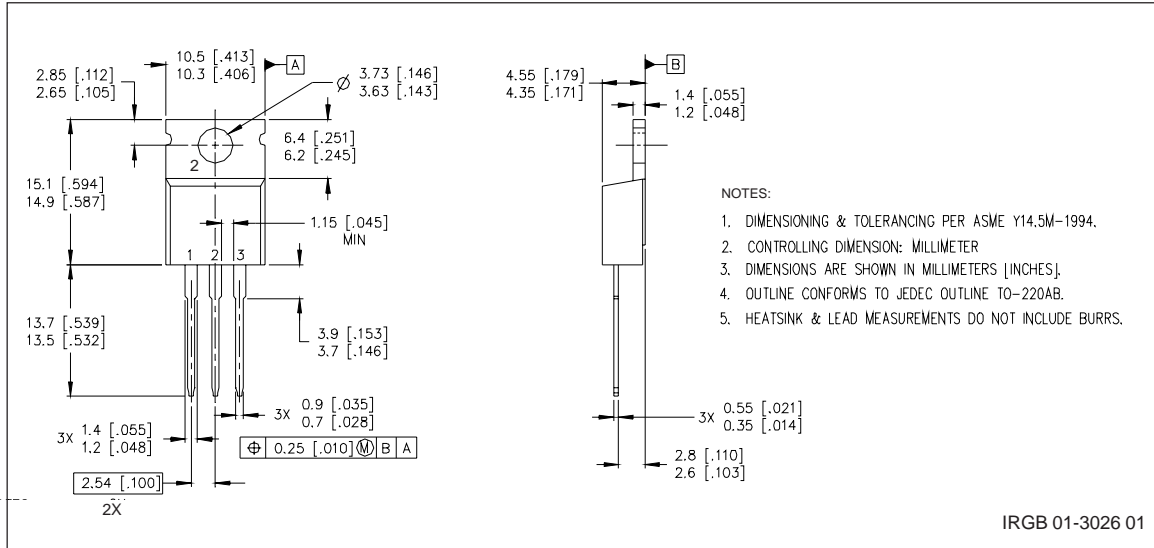
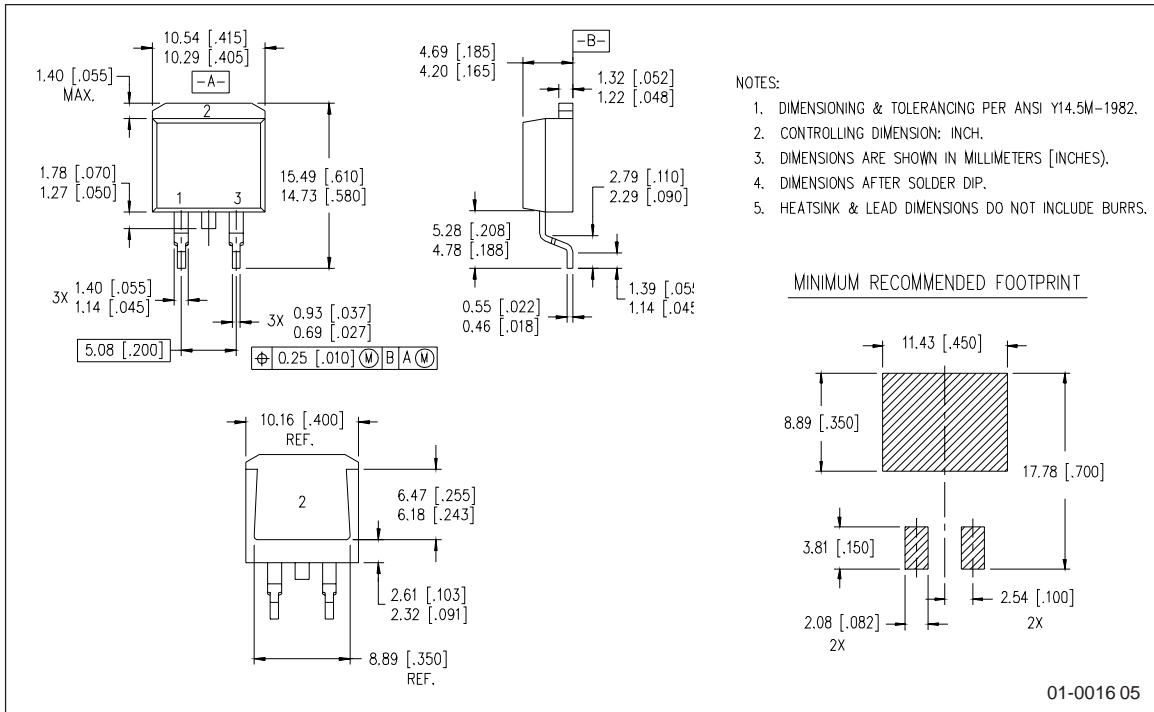


Figure 19 - Turn-on, Turn-off, and treset Vs Tjunction (°C)

Case Outline - TO-220



Case Outline - D²PAK (SMD220)



Tape & Reel - D²PAK (SMD220)

